

2SA2026

FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

2SA2026 is a silicon PNP epitaxial type transistor. It is designed with high voltage application.

FEATURE

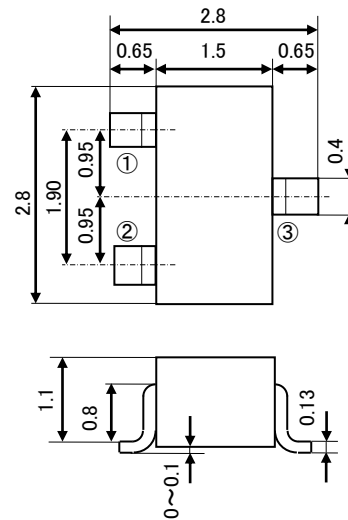
- Small collector to emitter saturation voltage
 $V_{CE(sat)} = -0.5V$ max (@ $I_C = -100mA$, $I_B = -10mA$)
- Small package for easy mounting

APPLICATION

Hybrid IC, DC-DC converter

OUTLINE DRAWING

UNIT: mm



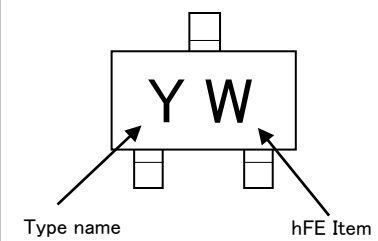
TERMINAL CONNECTER

- ①: BASE JEITA: SC-59
②: EMITTER JEDEC: Similar to TO-236
③: COLLECTOR

MAXIMUM RATING ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to Base voltage	-300	V
V_{EBO}	Emitter to Base voltage	-7	V
V_{CEO}	Collector to Emitter voltage	-300	V
I_C	Collector current	-100	mA
P_C	Collector dissipation ($T_a = 25^\circ C$)	200	mW
T_j	Junction temperature	+150	$^\circ C$
T_{stg}	Storage temperature	-55 ~ +150	$^\circ C$

MARKING

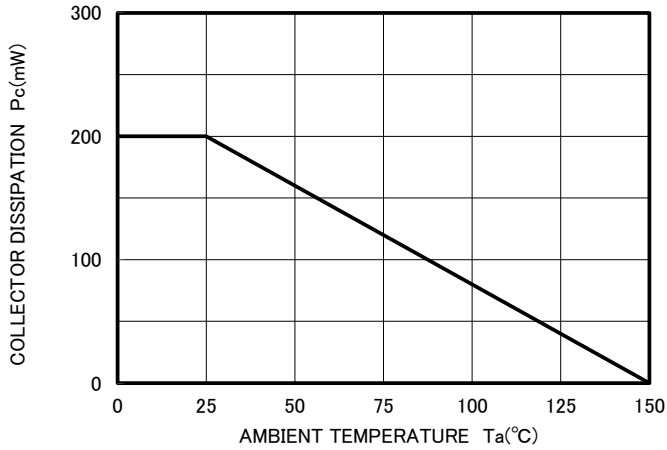


ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

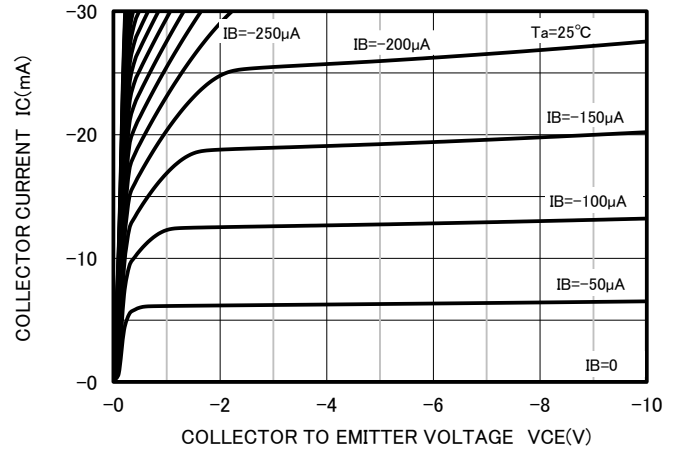
SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CBO}$	C to B breakdown voltage	$I_C = -50 \mu A$, $I_E = 0mA$	-300	-	-	V
$V_{(BR)EBO}$	E to B breakdown voltage	$I_E = -50 \mu A$, $I_C = 0mA$	-7	-	-	V
$V_{(BR)CEO}$	C to E breakdown voltage	$I_C = -1mA$, $R_{BE} = \infty$	-300	-	-	V
I_{CBO}	Collector cut off current	$V_{CB} = -300V$, $I_E = 0mA$	-	-	-0.5	μA
I_{EBO}	Emitter cut off current	$V_{EB} = -5V$, $I_C = 0mA$	-	-	-0.5	μA
hFE	DC forward current gain	$V_{CE} = -10V$, $I_C = -10mA$	50	-	305	-
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -100mA$, $I_B = -10mA$	-	-	-0.5	V
fT	Gain bandwidth product	$V_{CE} = -6V$, $I_E = 10mA$	-	40	-	MHz
Cob	Collector output capacitance	$V_{CE} = -6V$, $I_E = 0mA$, $f = 1MHz$	-	3.0	-	pF

TYPICAL CHARACTERISTICS

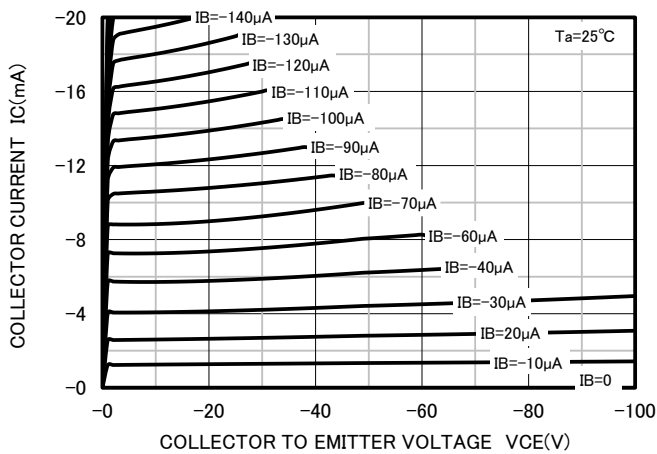
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



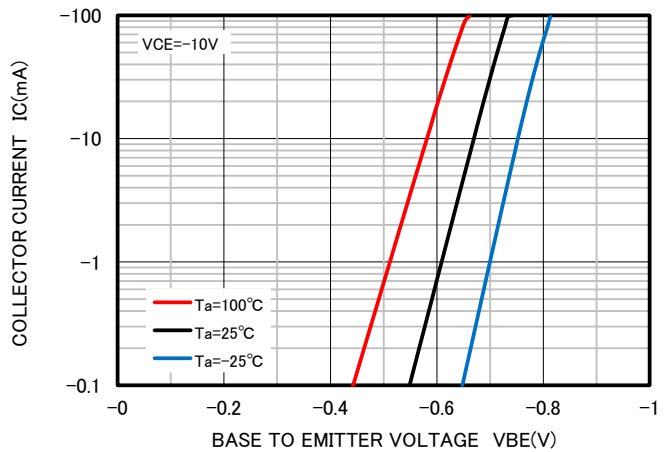
COMMON EMITTER OUTPUT(1)



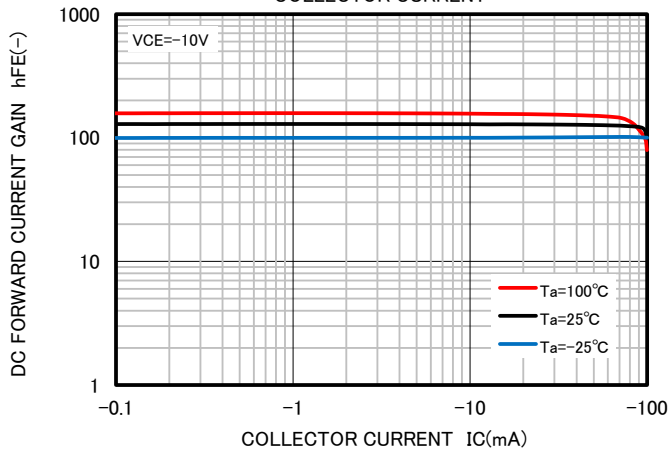
COMMON EMITTER OUTPUT (2)



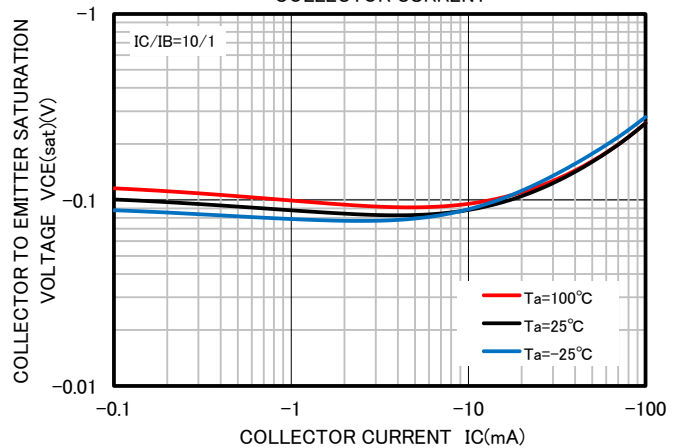
COMMON EMITTER TRANSFER



DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



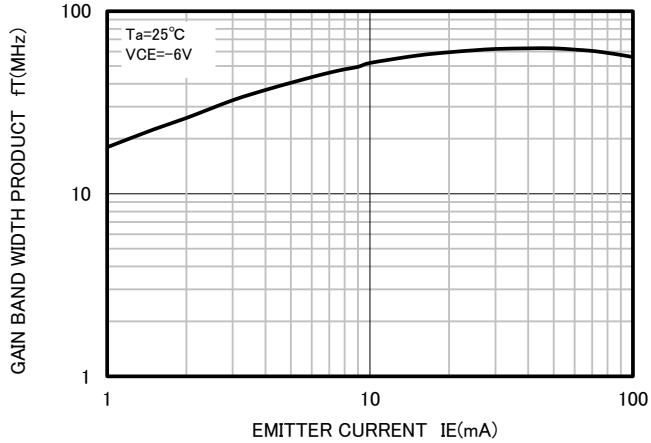
COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



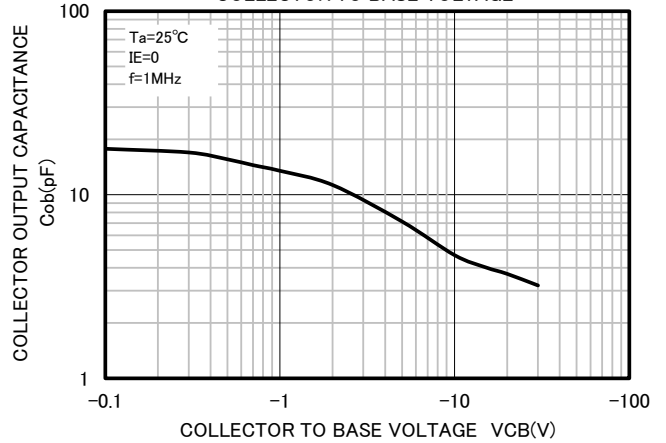
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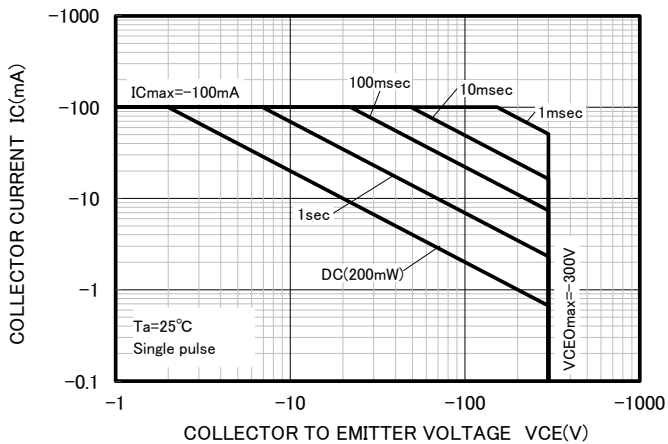
GAIN BAND WIDTH PRODUCT VS.
EMITTER CURRENT



COLLECTOR OUTPUT CAPACITANCE VS.
COLLECTOR TO BASE VOLTAGE



ASO



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